

## Product Summary

Device	BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> MAX T <sub>A</sub> = +25°C
Q1 N-Channel	20V	25mΩ @ V <sub>GS</sub> = 4.5V	6.0A
		35mΩ @ V <sub>GS</sub> = 2.5V	5.1A
Q2 P-Channel	-20V	75mΩ @ V <sub>GS</sub> = -4.5V	-3.5A
		140mΩ @ V <sub>GS</sub> = -2.5V	-2.5A

## Features

- PCB Footprint of 4mm<sup>2</sup>
- Low On-Resistance
- Low Input Capacitance
- Low Profile, 0.6mm Maximum Height
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMC2025UFDBQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**

<https://www.diodes.com/quality/product-definitions/>

## Description and Applications

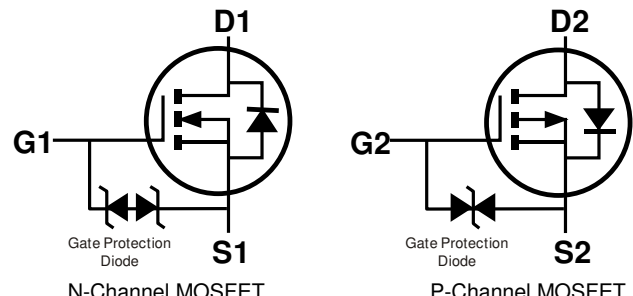
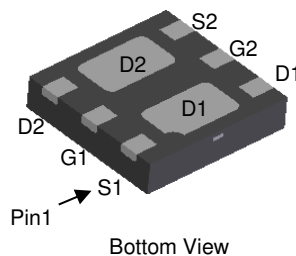
This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- Load Switch
- Power Management Functions
- Portable Power Adaptors

## Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 <sup>(e4)</sup>
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)

U-DFN2020-6 (Type B)



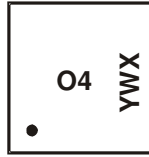
Internal Schematic

## Ordering Information (Note 4)

Part Number	Case	Packaging
DMC2025UFDBQ-7	U-DFN2020-6 (Type B)	3,000/Tape & Reel
DMC2025UFDBQ-13	U-DFN2020-6 (Type B)	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



O4 = Product Type Marking Code  
 YWX = Date Code Marking  
 Y = Year (ex: 1 = 2021)  
 W = Week (ex: a = Week 27; z Represents Week 52 and 53)  
 X = Internal Code (ex: U = Monday)

### Date Code Key

Year	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032
Code	1	2	3	4	5	6	7	8	9	0	1	2

Week	1-26	27-52	53
Code	A-Z	a-z	z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	T	U	V	W	X	Y	Z

## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Q1	Q2	Unit		
		N-CHANNEL	P-CHANNEL			
Drain-Source Voltage	V <sub>DSS</sub>	20	-20	V		
Gate-Source Voltage	V <sub>GSS</sub>	±10	±8	V		
Continuous Drain Current (Note 6)	I <sub>D</sub>	6.0	-3.5	A		
N-Channel: V <sub>GS</sub> = 4.5V					Steady State	T <sub>A</sub> = +25°C
P-Channel: V <sub>GS</sub> = -4.5V						
Maximum Continuous Body Diode Forward Current (Note 6)	I <sub>S</sub>	2	-1.0	A		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	20	-10	A		
Avalanche Current (L = 0.1mH) (Note 7)	I <sub>AS</sub>	8	-13	A		
Avalanche Energy (L = 0.1mH) (Note 7)	E <sub>AS</sub>	8	8.5	mJ		

## Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	P <sub>D</sub>	0.7	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>θJA</sub>	178	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	1.4	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>θJA</sub>	92	°C/W
Thermal Resistance, Junction to Case (Note 6)		R <sub>θJC</sub>	30	
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>		-55 to +150	°C

Notes: 5. Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout.  
 6. Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate.  
 7. I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.

### Electrical Characteristics Q1 N-CHANNEL (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±10V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.5	—	1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	—	25	mΩ	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 4A
			—	35		
Diode Forward Voltage	V <sub>SD</sub>	—	0.7	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 5A
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>iss</sub>	—	486	—	pF	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	92	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	77	—		
Gate Resistance	R <sub>g</sub>	—	3.2	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	5.9	—	nC	V <sub>DS</sub> = 10V, I <sub>D</sub> = 6.5A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	12.3	—		
Gate-Source Charge	Q <sub>gs</sub>	—	0.8	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	2.2	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	3.4	—	ns	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 4.5V, R <sub>g</sub> = 6Ω, R <sub>L</sub> = 10Ω, I <sub>D</sub> = 1A
Turn-On Rise Time	t <sub>R</sub>	—	5.4	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	17.6	—		
Turn-Off Fall Time	t <sub>F</sub>	—	9.3	—		
Reverse Recovery Time	t <sub>RR</sub>	—	7.7	—	ns	I <sub>F</sub> = 1A, di/dt = 100A/μs
Reverse Recovery Charge	Q <sub>RR</sub>	—	1.5	—	nC	I <sub>F</sub> = 1A, di/dt = 100A/μs

Notes: 8. Short duration pulse test used to minimize self-heating effect.  
9. Guaranteed by design. Not subject to product testing.

**Electrical Characteristics Q2 P-CHANNEL** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	-20	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$	$I_{DSS}$	—	—	-1.0	$\mu A$	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 10$	$\mu A$	$V_{GS} = \pm 8V, V_{DS} = 0V$
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	-0.35	—	-1.4	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	—	75	m $\Omega$	$V_{GS} = -4.5V, I_D = -2.9A$
		—	—	140		$V_{GS} = -2.5V, I_D = -2.3A$
Diode Forward Voltage	$V_{SD}$	—	—	-1.2	V	$V_{GS} = 0V, I_S = -3.0A$
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	$C_{iss}$	—	642	—	pF	$V_{DS} = -10V, V_{GS} = 0V,$ $f = 1.0\text{MHz}$
Output Capacitance	$C_{oss}$	—	98	—	pF	
Reverse Transfer Capacitance	$C_{rss}$	—	87	—	pF	
Gate Resistance	$R_g$	—	26.5	—	$\Omega$	$V_{DS} = 0V, V_{GS} = 0V, f = 1\text{MHz}$
Total Gate Charge ( $V_{GS} = -4.5V$ )	$Q_g$	—	8.8	—	nC	$V_{DS} = -10V, I_D = -3.7A$
Total Gate Charge ( $V_{GS} = -8V$ )		—	15	—	nC	
Gate-Source Charge	$Q_{gs}$	—	0.9	—	nC	
Gate-Drain Charge	$Q_{gd}$	—	2.9	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	5.5	—	ns	
Turn-On Rise Time	$t_R$	—	22.6	—	ns	$V_{DD} = -10V, V_{GS} = -4.5V,$ $R_L = 3.3\Omega, R_g = 1\Omega$
Turn-Off Delay Time	$t_{D(OFF)}$	—	34.1	—	ns	
Turn-Off Fall Time	$t_F$	—	34.3	—	ns	
Body Diode Reverse Recovery Time	$t_{RR}$	—	13	—	ns	$I_S = -3.0A, dI/dt = 100A/\mu s$
Body Diode Reverse Recovery Charge	$Q_{RR}$	—	3.3	—	nC	$I_S = -3.0A, dI/dt = 100A/\mu s$

Notes: 8. Short duration pulse test used to minimize self-heating effect.  
9. Guaranteed by design. Not subject to product testing.

**Typical Characteristics - N-CHANNEL**

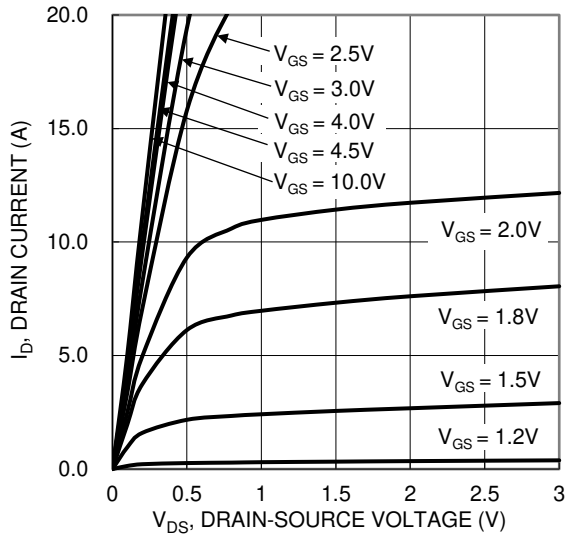


Figure 1. Typical Output Characteristic

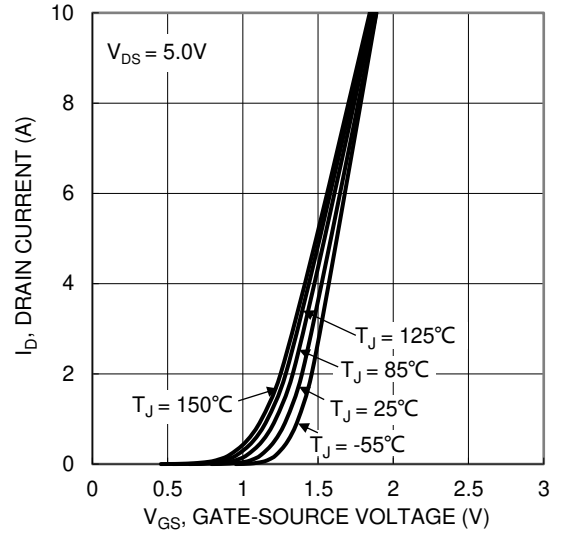


Figure 2. Typical Transfer Characteristic

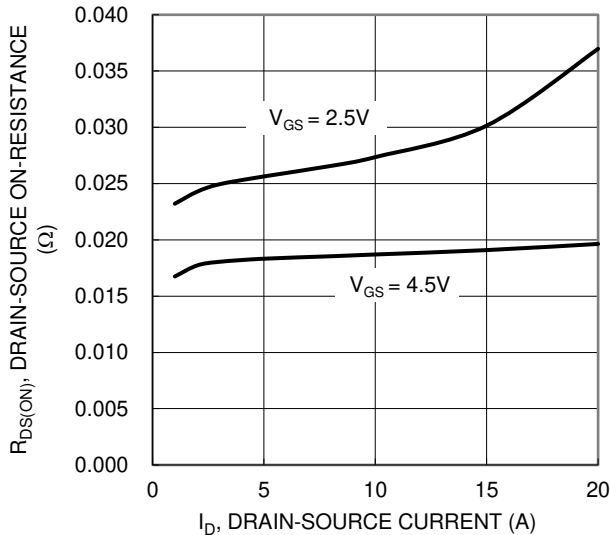


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

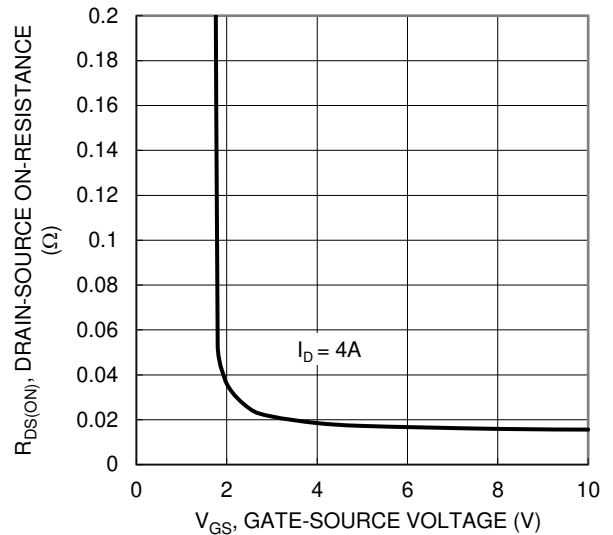


Figure 4. Typical Transfer Characteristic

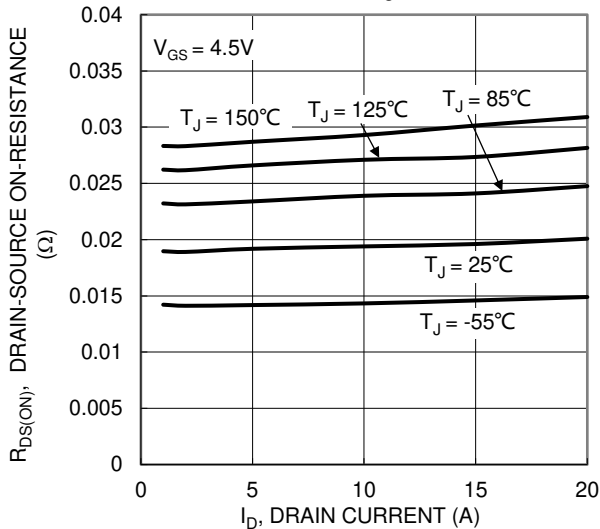


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

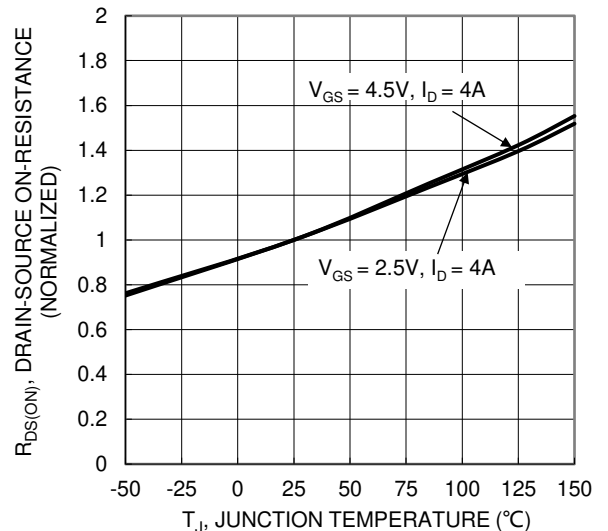


Figure 6. On-Resistance Variation with Temperature

**Typical Characteristics - N-CHANNEL** (continued)

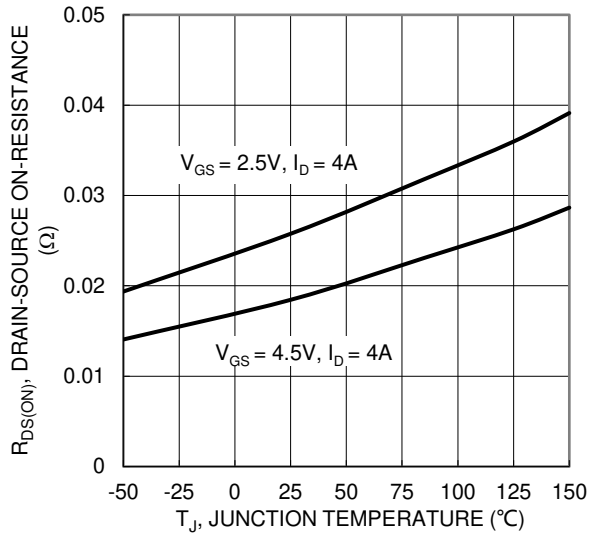


Figure 7. On-Resistance Variation with Temperature

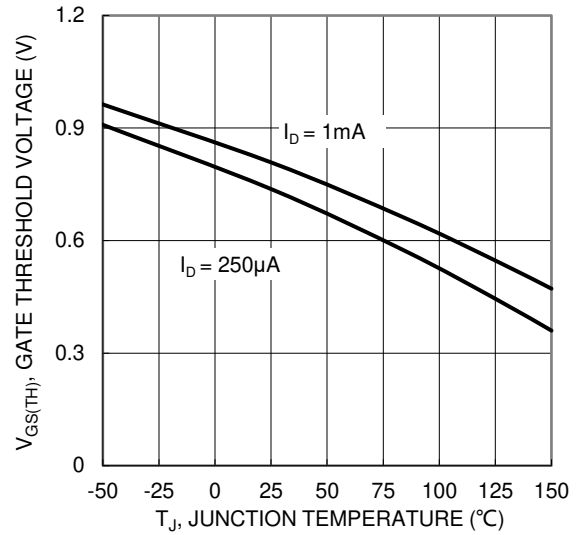


Figure 8. Gate Threshold Variation vs. Junction Temperature

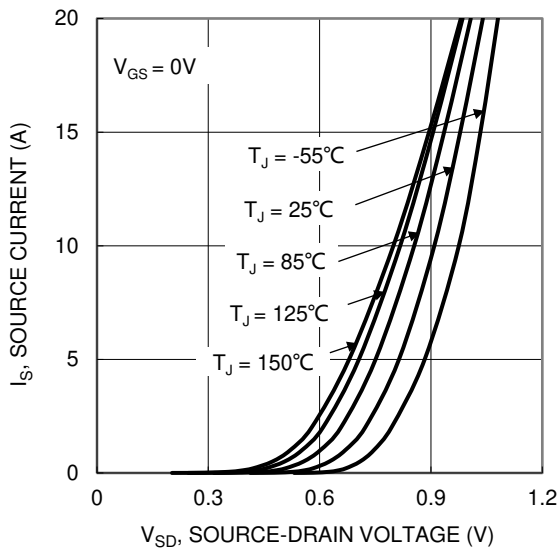


Figure 9. Diode Forward Voltage vs. Current

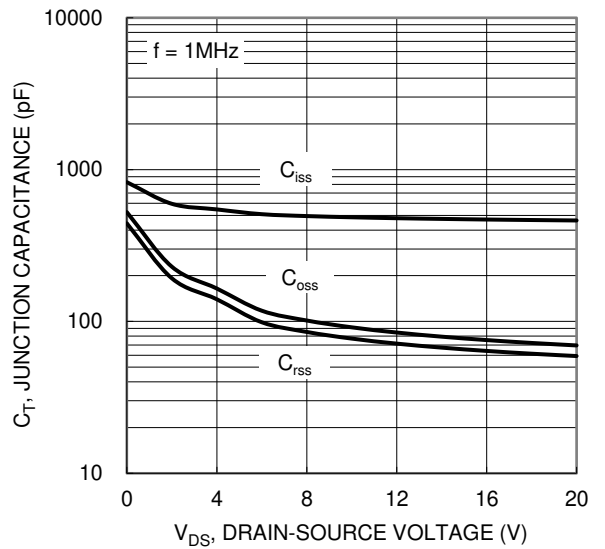


Figure 10. Typical Junction Capacitance

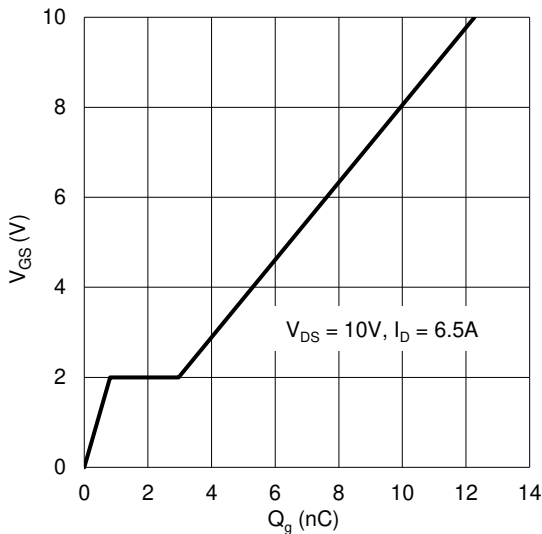


Figure 11. Gate Charge

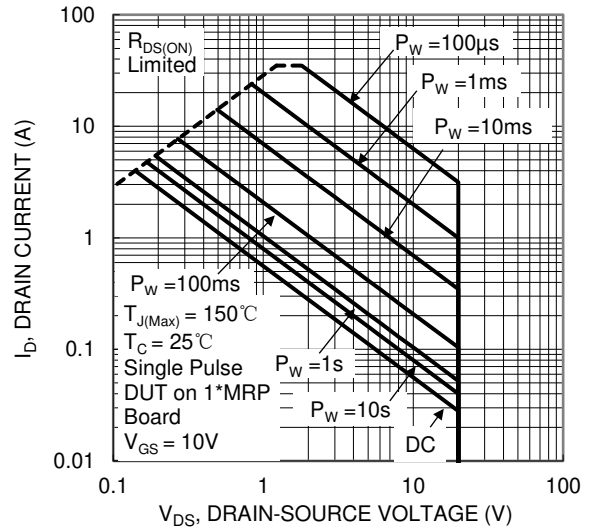


Figure 12. SOA, Safe Operation Area

**Typical Characteristics - P-CHANNEL**

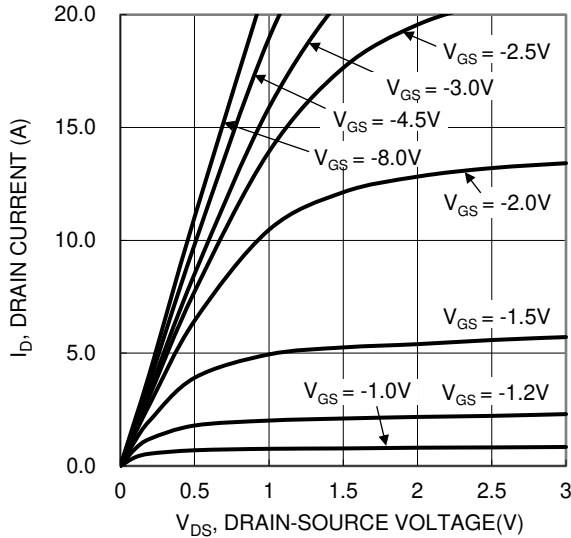


Figure 13. Typical Output Characteristic

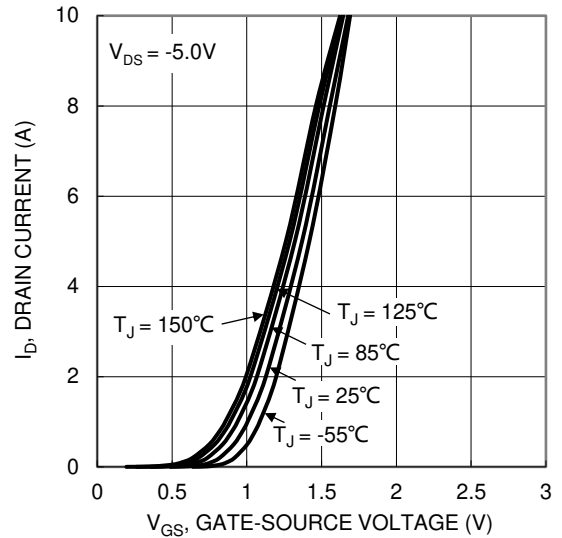


Figure 14. Typical Transfer Characteristic

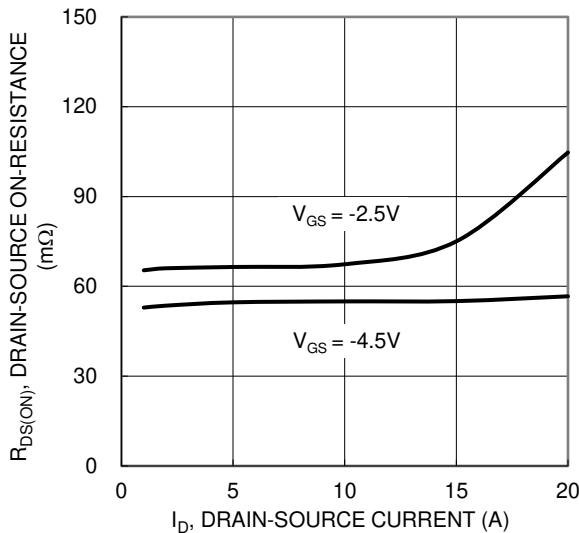


Figure 15. Typical On-Resistance vs. Drain Current and Gate Voltage

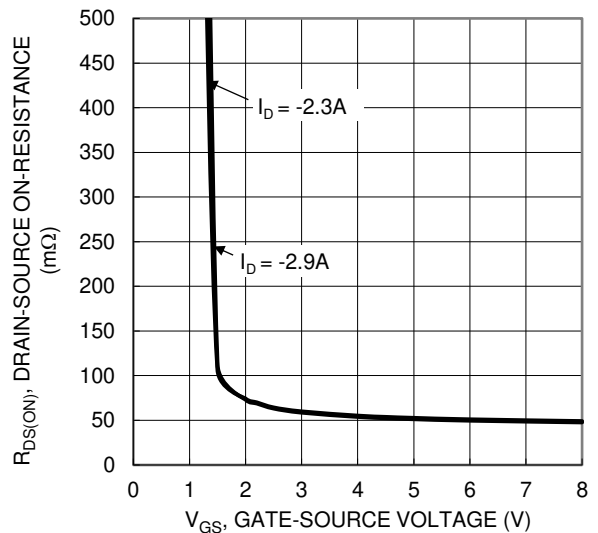


Figure 16. Typical Transfer Characteristic

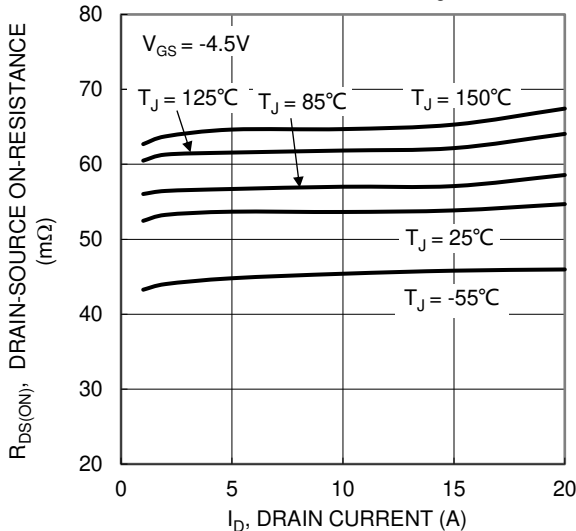


Figure 17. Typical On-Resistance vs. Drain Current and Temperature

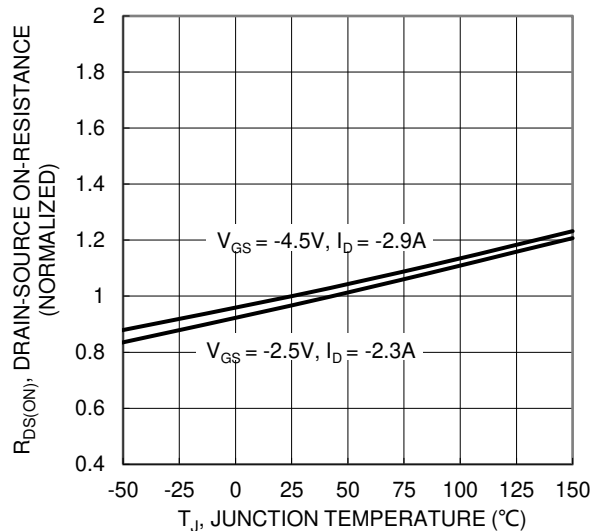


Figure 18. On-Resistance Variation with Temperature

**Typical Characteristics - P-CHANNEL** (continued)

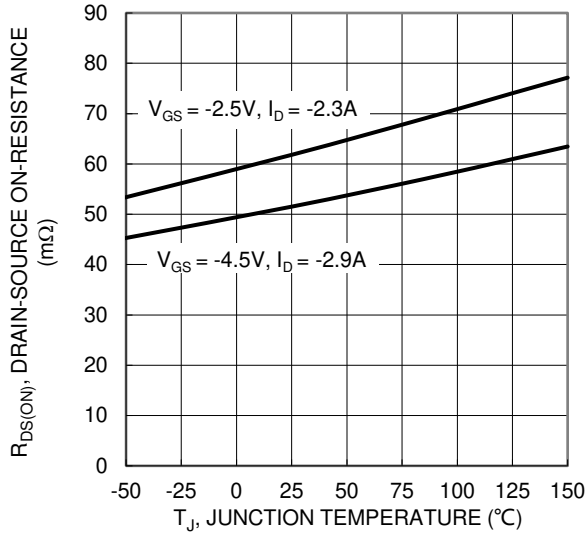


Figure 19. On-Resistance Variation with Temperature

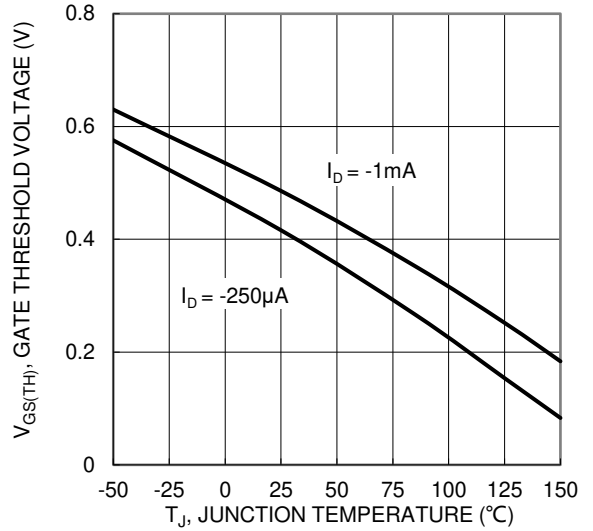


Figure 20. Gate Threshold Variation vs. Junction Temperature

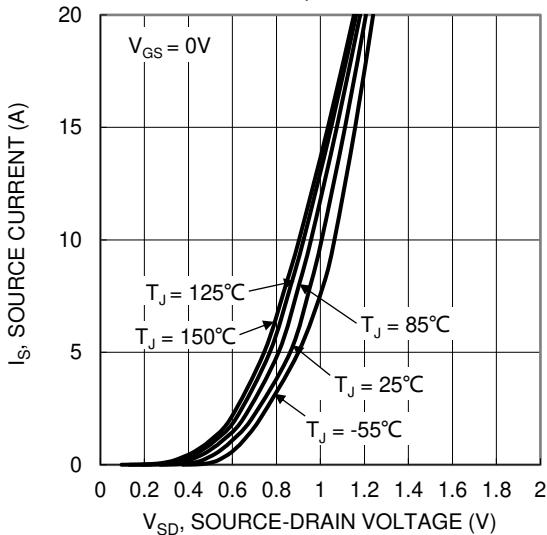


Figure 21. Diode Forward Voltage vs. Current

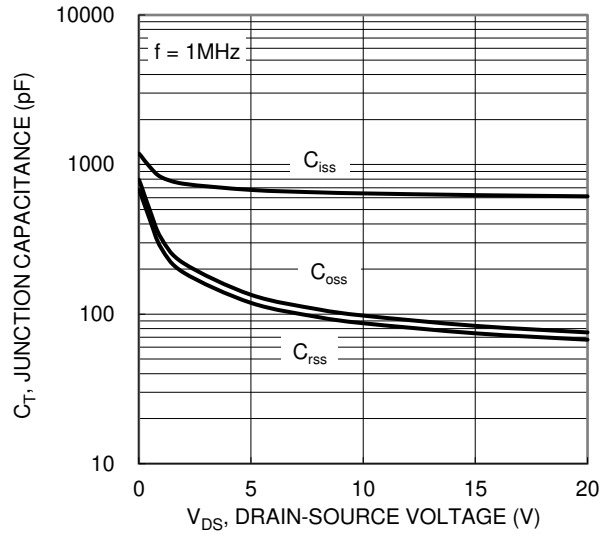


Figure 22. Typical Junction Capacitance

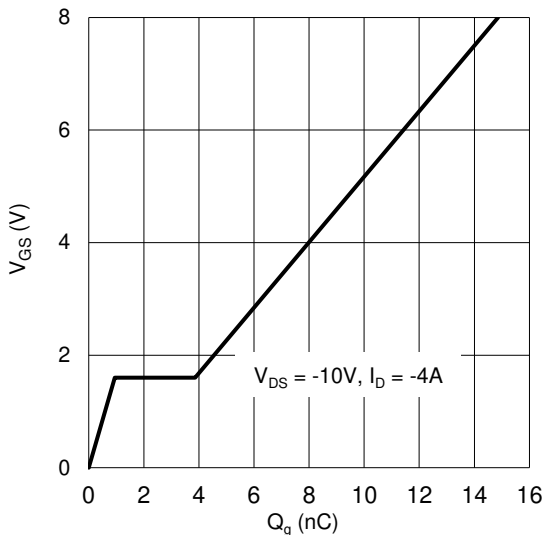


Figure 23. Gate Charge

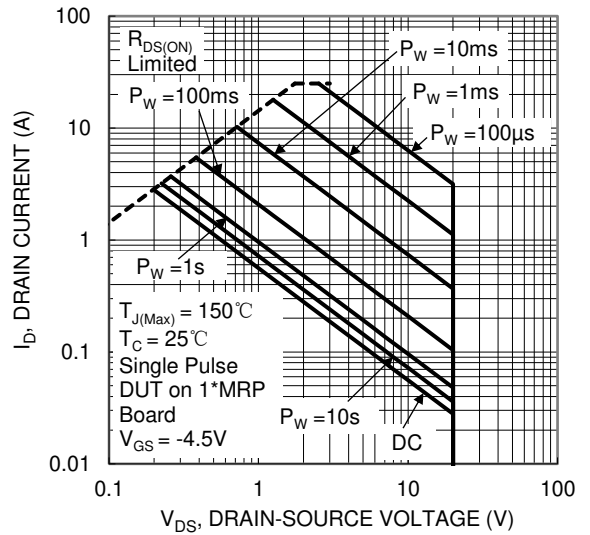


Figure 24. SOA, Safe Operation Area



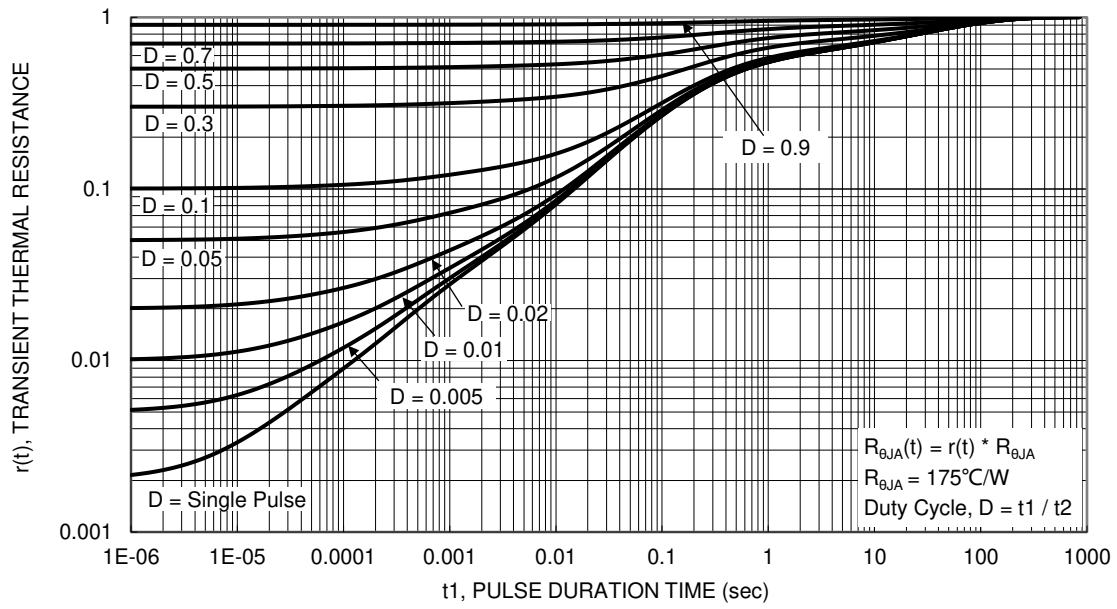
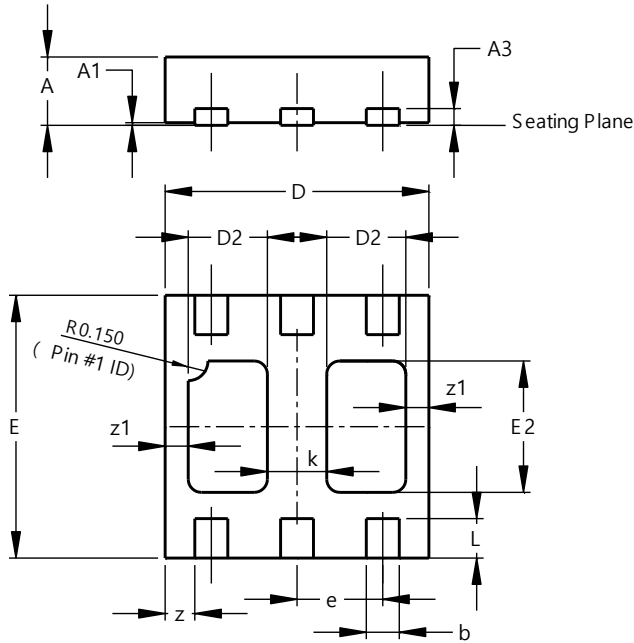


Figure 25. Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**U-DFN2020-6 (Type B)**

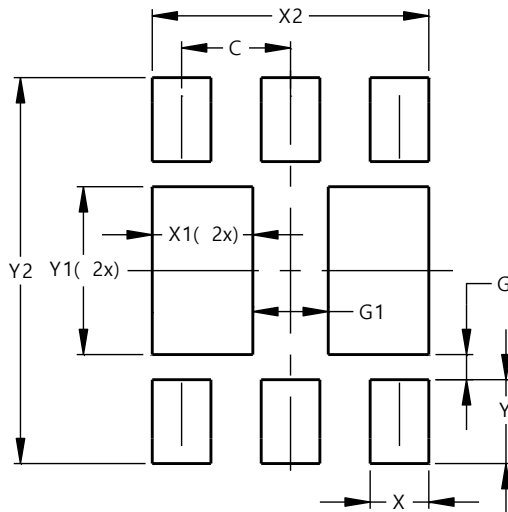


U-DFN2020-6 Type B			
Dim	Min	Max	Typ
A	0.545	0.605	0.575
A1	0.00	0.05	0.02
A3	-	-	0.13
b	0.20	0.30	0.25
D	1.95	2.075	2.00
D2	0.50	0.70	0.60
e	-	-	0.65
E	1.95	2.075	2.00
E2	0.90	1.10	1.00
k	-	-	0.45
L	0.25	0.35	0.30
z	-	-	0.225
z1	-	-	0.175
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**U-DFN2020-6 (Type B)**



Dimensions	Value (in mm)
C	0.650
G	0.150
G1	0.450
X	0.350
X1	0.600
X2	1.650
Y	0.500
Y1	1.000
Y2	2.300

**IMPORTANT NOTICE**

1. DIODES INCORPORATED AND ITS SUBSIDIARIES (“DIODES”) MAKE NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO ANY INFORMATION CONTAINED IN THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).
2. The Information contained herein is for informational purpose only and is provided only to illustrate the operation of Diodes products described herein and application examples. Diodes does not assume any liability arising out of the application or use of this document or any product described herein. This document is intended for skilled and technically trained engineering customers and users who design with Diodes products. Diodes products may be used to facilitate safety-related applications; however, in all instances customers and users are responsible for (a) selecting the appropriate Diodes products for their applications, (b) evaluating the suitability of the Diodes products for their intended applications, (c) ensuring their applications, which incorporate Diodes products, comply the applicable legal and regulatory requirements as well as safety and functional-safety related standards, and (d) ensuring they design with appropriate safeguards (including testing, validation, quality control techniques, redundancy, malfunction prevention, and appropriate treatment for aging degradation) to minimize the risks associated with their applications.
3. Diodes assumes no liability for any application-related information, support, assistance or feedback that may be provided by Diodes from time to time. Any customer or user of this document or products described herein will assume all risks and liabilities associated with such use, and will hold Diodes and all companies whose products are represented herein or on Diodes’ websites, harmless against all damages and liabilities.
4. Products described herein may be covered by one or more United States, international or foreign patents and pending patent applications. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks and trademark applications. Diodes does not convey any license under any of its intellectual property rights or the rights of any third parties (including third parties whose products and services may be described in this document or on Diodes’ website) under this document.
5. Diodes products are provided subject to Diodes’ Standard Terms and Conditions of Sale (<https://www.diodes.com/about/company/terms-and-conditions/terms-and-conditions-of-sales/>) or other applicable terms. This document does not alter or expand the applicable warranties provided by Diodes. Diodes does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel.
6. Diodes products and technology may not be used for or incorporated into any products or systems whose manufacture, use or sale is prohibited under any applicable laws and regulations. Should customers or users use Diodes products in contravention of any applicable laws or regulations, or for any unintended or unauthorized application, customers and users will (a) be solely responsible for any damages, losses or penalties arising in connection therewith or as a result thereof, and (b) indemnify and hold Diodes and its representatives and agents harmless against any and all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim relating to any noncompliance with the applicable laws and regulations, as well as any unintended or unauthorized application.
7. While efforts have been made to ensure the information contained in this document is accurate, complete and current, it may contain technical inaccuracies, omissions and typographical errors. Diodes does not warrant that information contained in this document is error-free and Diodes is under no obligation to update or otherwise correct this information. Notwithstanding the foregoing, Diodes reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes.
8. Any unauthorized copying, modification, distribution, transmission, display or other use of this document (or any portion hereof) is prohibited. Diodes assumes no responsibility for any losses incurred by the customers or users or any third parties arising from any such unauthorized use.

Copyright © 2021 Diodes Incorporated

[www.diodes.com](http://www.diodes.com)